# **ACT108W-600E**

# AC Thyristor power switch Rev. 5 — 13 July 2010

Product data sheet

#### 1. **Product profile**

### 1.1 General description

AC Thyristor power switch in a SOT223 surface-mountable plastic package with self-protective capabilities against low and high energy transients

### 1.2 Features and benefits

- Common terminal on mounting base allows multiple ACTs on shared cooling pad
- Exclusive negative gate triggering
- Full cycle AC conduction
- Remote gate separates the gate driver from the effects of the load current
- Safe clamping of low energy over-voltage transients
- Self-protective turn-on during high energy voltage transients
- Surface-mountable package
- Very high noise immunity

### 1.3 Applications

- Contactors, circuit breakers, valves, dispensers and door locks
- Fan motor circuits

- Lower-power highly inductive, resistive and safety loads
- Pump motor circuits

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	-	600	V
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 100 \text{ mA;}$ LD+ G-; $T_j = 25 \text{ °C;}$ see <u>Figure 10</u>	1	-	10	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 100 mA; LD- G-; T <sub>j</sub> = 25 °C	1	-	10	mA
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{sp} \le 112 ^{\circ}\text{C}$ ; see <u>Figure 4</u> ; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	-	0.8	Α
dV <sub>D</sub> /dt	rate of rise of off-state voltage	V <sub>DM</sub> = 402 V; T <sub>j</sub> = 125 °C; gate open circuit; see Figure 14	1000	-	-	V/µs



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CL}$	clamping voltage	$I_{CL}$ = 100 $\mu$ A; $t_p$ = 1 ms; $T_j \le$ 125 °C; see <u>Figure 17</u>	650	-	-	V
$V_{PP}$	peak pulse voltage	$T_j = 25$ °C; non-repetitive, off-state; see Figure 3	-	-	2	kV
$V_{T}$	on-state voltage	I <sub>T</sub> = 1.1 A; see <u>Figure 13</u>	-	-	1.3	V

# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	LD	load		1.0
2	CM	common	4	LD
3	G	gate		G—OF
4	СМ	common	1 2 3	СМ
			SOT223 (SC-73)	001aaj924

## 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
ACT108W-600E	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	600	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>sp</sub> ≤ 112 °C; see <u>Figure 4</u> ; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	0.8	Α
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 16.7 \text{ ms}$	-	8.8	Α
		full sine wave; T <sub>j(init)</sub> = 25 °C; t <sub>p</sub> = 20 ms; see <u>Figure 5</u> ; see <u>Figure 6</u>	-	8	Α
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; sine-wave pulse	-	0.32	A <sup>2</sup> s
dI <sub>T</sub> /dt	rate of rise of on-state current	$I_T = 1 \text{ A}$ ; $I_G = 20 \text{ mA}$ ; $dI_G/dt = 0.2 \text{ A/}\mu\text{s}$	-	100	A/µs
I <sub>GM</sub>	peak gate current	t = 20 μs	-	1	Α
$V_{GM}$	peak gate voltage	positive applied gate voltage	-	15	V
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.1	W
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C
$V_{PP}$	peak pulse voltage	$T_j = 25$ °C; non-repetitive, off-state; see Figure 3	-	2	kV

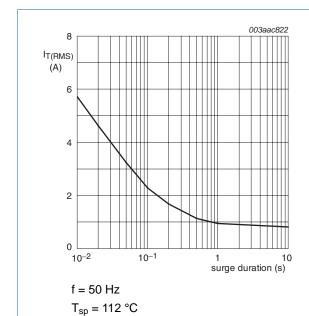


Fig 1. RMS on-state current as a function of surge duration; maximum values

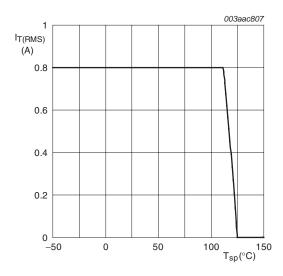


Fig 2. RMS on-state current as a function of solder point temperature; maximum values

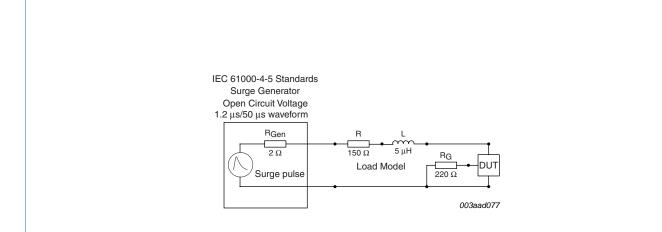


Fig 3. Test circuit for inductive and resistive loads with conditions equivalent to IEC 61000-4-5

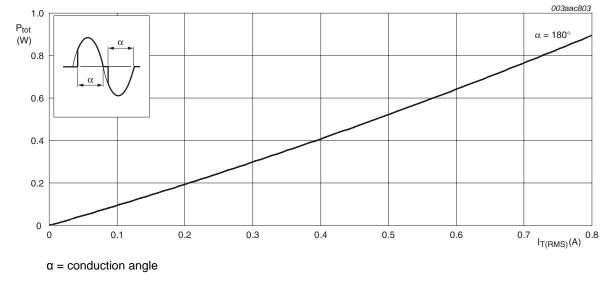


Fig 4. Total power dissipation as a function of RMS on-state current; maximum values

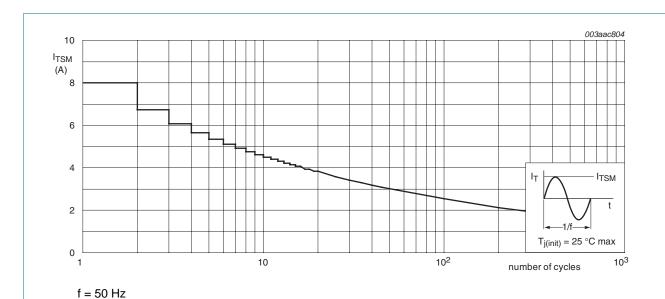


Fig 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

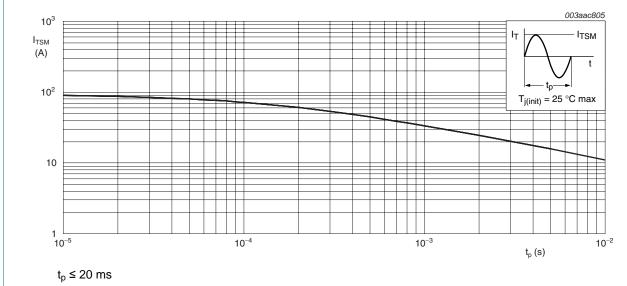
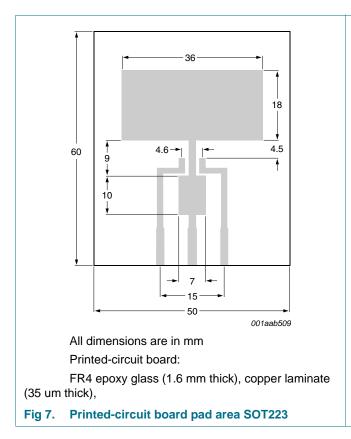


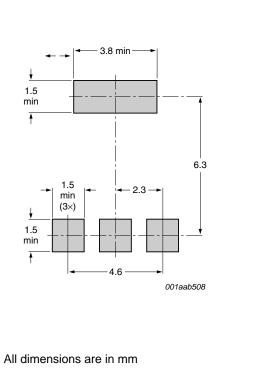
Fig 6. Non-repetitive peak on-state current as a function of pulse width; maximum values

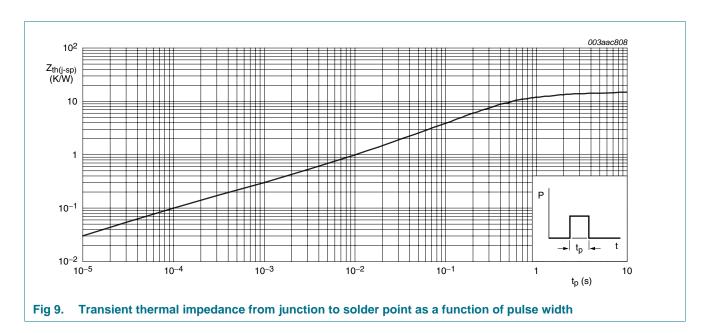
### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point	full cycle with heatsink compound; see Figure 9	-	-	15	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to	full cycle; printed-circuit board mounted for pad area; see Figure 7	-	70	-	K/W
	ambient	full cycle; printed-circuit board mounted for minimum footprint; see Figure 8	-	156	-	K/W







### 6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 100 \text{ mA; LD+ G-;}$ $T_j = 25 \text{ °C; see } \frac{\text{Figure } 10}{\text{Figure } 10}$	1	-	10	mA
		$V_D = 12 \text{ V}; I_T = 100 \text{ mA}; LD- G-;$ $T_j = 25 \text{ °C}$	1	-	10	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 12 \text{ mA}; T_j = 25 \text{ °C};$ see <u>Figure 11</u>	-	-	30	mA
I <sub>H</sub>	holding current	$V_D = 12 \text{ V}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 12}{}$	-	9	25	mA
$V_{T}$	on-state voltage	I <sub>T</sub> = 1.1 A; see <u>Figure 13</u>	-	-	1.3	V
$V_{GT}$	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 100 \text{ mA}; T_j \le 125 \text{ °C}$	0.15	-	-	V
		$V_D = 12 \text{ V}; I_T = 100 \text{ mA}; T_j = 25 \text{ °C}$	-	-	1	V
I <sub>D</sub>	off-state current	$V_D = 600 \text{ V}; T_j \le 125 ^{\circ}\text{C}$	-	-	0.2	mΑ
		$V_D = 600 \text{ V}; T_j \le 25 ^{\circ}\text{C}$	-	-	2	μΑ
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; $T_j$ = 125 °C; gate open circuit; see Figure 14	1000	-	-	V/µs
dI <sub>com</sub> /dt	rate of change of commutating current	$V_D = 400 \text{ V}; T_j = 125 \text{ °C}; I_{T(RMS)} = 1 \text{ A};$ $dV_{com}/dt = 15 \text{ V/}\mu\text{s}; gate open circuit;}$ see <u>Figure 15</u> ; see <u>Figure 16</u>	0.3	-	-	A/ms
V <sub>CL</sub>	clamping voltage	$I_{CL}$ = 100 $\mu$ A; $t_p$ = 1 ms; $T_j \le$ 125 °C; see <u>Figure 17</u>	650	-	-	V

150

T<sub>i</sub> (°C)

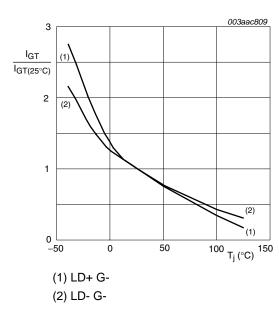


Fig 11. Normalized latching current as a function of junction temperature

50

3

2

1

0 └ -50

ΙL

I<sub>L(25°C)</sub>

Fig 10. Normalized gate trigger current as a function of junction temperature

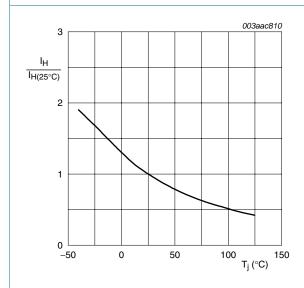
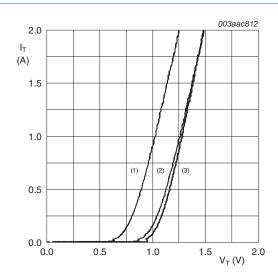


Fig 12. Normalized holding current as a function of junction temperature

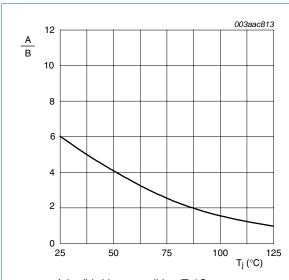


 $V_{O} = 0.758 \text{ V}; \text{ R}_{S} = 0.263 \Omega$ 

(1) $T_j$  = 125 °C; typical values (2) $T_j$  = 125 °C; maximum values

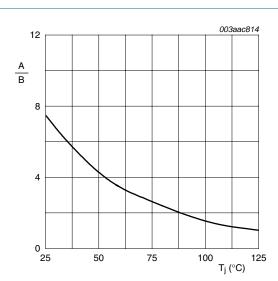
(3)T<sub>i</sub> = 25 °C; maximum values

Fig 13. On-state current as a function of on-state voltage



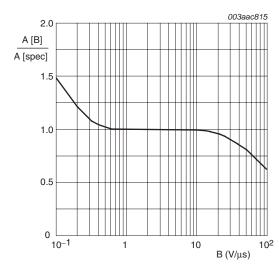
A is  $dV_D/dt$  at condition  $T_j$  °C B is  $dV_D/dt$  at condition  $T_i$  125 °C

Fig 14. Normalized rate of rise of off-state voltage as a function of junction temperature



A is  $dI_{com}/dt$  at condition  $T_j$  °C B is  $dI_{com}/dt$  at condition  $T_j$  125 °C  $V_D = 400 \text{ V}$ 

Fig 15. Normalized critical rate of rise of commutating current as a function of junction temperature



A[B] is  $dI_{com}/dt$  at condition B,  $dV_{com}/dt$ A[spec] is the specified data sheet value of  $dI_{com}/dt$ turn-off time < 20 ms

Fig 16. Normalized critical rate of change of commutating current as a function of critical rate of change of commutating voltage; minimum values

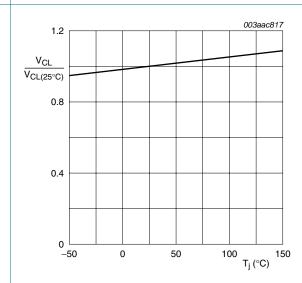


Fig 17. Normalized clamping voltage (upper limit) as a function of junction temperature; minimum values

### 7. Package outline

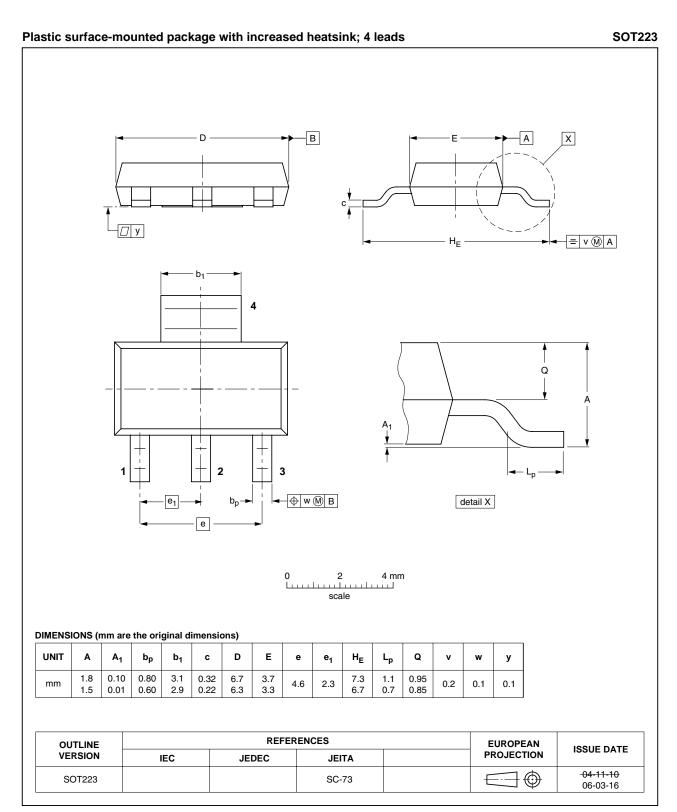


Fig 18. Package outline SOT223 (SC-73)

ACT108W-600E

# 8. Revision history

### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
ACT108W-600E v.5	20100713	Product data sheet	-	ACT108W-600E v.4
Modifications:	<ul> <li>Various change</li> </ul>	es to content.		
ACT108W-600E v.4	20091209	Product data sheet	-	-

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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